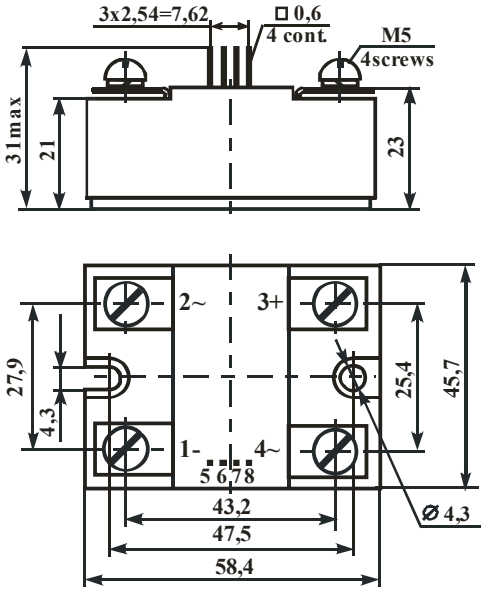
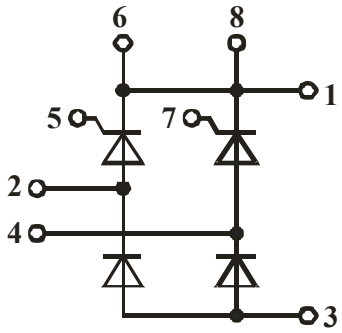
SINGLE-PHASE THYRISTOR-DIODE BRIDGE MODULE
M20-63-12

DATASHEET IN BRIEF

Single-phase thyristor-diode bridge module with thyristors control, connected to "positive" output, is intended for rectifying (for use it as a control rectifier).

OVERALL DRAWING AND ELECTRIC CIRCUIT





BASIC CHARACTERISTICS

T = 25 °C

Product name	Pulse voltage: on-state/ direct diode, U_{TM} / U_{FM}, V		Off-state current /valve DC, I_D / I_R, mA		Thyristor hold-on current, I_H, mA	Thyristor turn-on current, I_I, mA	Thyristor gate trigger DC voltage, U_{GT}, V	Thyristor gate trigger DC, I_{GT}, mA	Electric isolation strength at DC between radiator and outputs, U_{ISOL}, V		Thyristor non-trigger DC voltage, U_{GD}, V T_j = 125 °C	Thermal junction-radiator resistance Rth(j-c), °C/W	
												thyristor	diode
	max	I_O, A amplit. value	max	U_O, V	max	max	max	max	min	t, minute	max	max	max
M20-63-12	1.65	$\frac{\pi}{2} \bullet I_O$, 10 ms, 50 Hz, sinus	1.5	± 1200	200	400	3.0	200	4000	1	0.25	1.0	1.3

MAXIMUM ALLOWABLE OPERATING MODES

Product name	Pulse non-repetitive voltage: Thyristor off-state/ reverse diode, U_{DSM} / U_{RSM}, V	Pulse repetitive voltage: off-state / reverse diode, U_{DRM} / U_{RRM}, V	Average rectified current, I_O, A Tr=75 °C	Linear voltage (rms.), Ulin, V	Non-repetitive surge DC, I_{TSM} I_{FSM}, A		Maximum switching frequency, kHz	Critical rate of rise of reverse voltage, $(du_R / dt)cr$, V/µs	DC critical rate of rise, $(di_T / dt)cr$, A/µs	Junction temperature T_{VJ} *, °C	
						t, ms					
	max	max	max	max	max			max	max	min	max
M20-63 - 12	± 1300	± 1200	63	840	300	10	3	1000	150	- 40	+125
*the modules are designed for operating in the equipment with using of coolers that support transition temperature in the prescribed ranges											

Precious metals are not contained

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